



ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>



## NTE2676 Silicon NPN Transistor High Voltage, High Speed Switch TO3P(H)IS Type Package

**Features:**

- High Breakdown Voltage:  $V_{CBO} = 1500V$  Min
- High Switching Speed
- Low Saturation Voltage

**Applications:**

- Color TV Horizontal Deflection Output

**Absolute Maximum Ratings:** ( $T_A = +25^{\circ}C$  unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	1500V
Collector–Emitter Voltage, $V_{CEO}$ .....	600V
Emitter–Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$	
Continuous .....	10A
Pulse .....	20A
Continuous Base Current, $I_B$ .....	5A
Collector Power Dissipation ( $T_C = +25^{\circ}C$ ), $P_C$ .....	50W
Operating Junction Temperature, $T_J$ .....	$+150^{\circ}C$
Storage Temperature Range, $T_{stg}$ .....	$-55^{\circ}$ to $+150^{\circ}C$

**Electrical Characteristics:** ( $T_C = +25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 6A, I_B = 1.5A$	–	–	3.0	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 6A, I_B = 1.5A$	–	–	1.4	V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 1500V, I_E = 0$	–	–	1.0	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	–	–	10	$\mu A$
DC Current Gain	h <sub>FE</sub>	$I_C = 1A, V_{CE} = 5V$	10	–	30	
		$I_C = 6A, V_{CE} = 5V$	4	–	8	
Current Gain Bandwidth Product	f <sub>T</sub>	$I_C = 100mA, V_{CE} = 10V$	–	1.7	–	MHz
Output Capacitance	C <sub>OB</sub>	$I_E = 0, V_{CB} = 10V, f_{test} = 1.0MHz$	–	135	–	pF
Storage Time	t <sub>stg</sub>	$I_{CP} = 6A, I_{B1(end)} = 1.5A, f_H = 15.75kHz$	–	–	11	$\mu s$
Fall Time	t <sub>f</sub>		–	–	0.7	$\mu s$

